

Features

- Low Forward Voltage (V_F) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Increased Creepage / Clearance + HV-H3TRB Rugged

Applications

- Battery Chargers
- Solar & Renewable Energy Power Conversion
- Industrial Power Supplies
- Boost Diodes in PFC & DC-DC







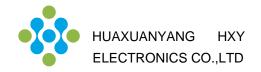


TO247-2L **Package**



Maximum Ratings ($T_c = 25$ °C unless otherwise specified)

Parameter	Symbol	Value	Unit	Test Conditions	Note	
Repetitive Peak Reverse Voltage	V_{RRM}	1200	\/			
DC Blocking Voltage	V _{DC}	1200	V			
		128		T _J = 25 °C		
Continuous Forward Current	I _F	88		T _J = 100 °C	Fig. 3	
		41		T _J = 155 °C		
Repetitive Peak Forward		161	Α	T _C = 25 °C, t _p = 10 ms, Half Sine Pulse		
Surge Current	FRM	91		T _C = 110 °C, t _p = 10 ms, Half Sine Pulse		
Non-Repetitive Forward		247		T _C = 25 °C, t _p = 10 ms, Half Sine Pulse		
Surge Current	FSM	245		T _C = 110 °C, t _p = 10 ms, Half Sine Pulse		
Power Dissipation	P _{tot}	667	W	T _c = 25 °C	Fig. 4	
		289		T _c = 110 °C		
i²t Value	∫ i²t	305	A ² s	T _c = 25 °C, t _p = 10 ms		
		300		T _c = 110 °C, t _p = 10 ms		



Electrical Characteristics

Parameter	Symbol	Тур.	Max.	Units	Test Conditions	Note	
Forward Voltage		1.5	1.8	V	I _F = 40 A, T _J = 25 °C	Fig. 1	
Forward Voltage	V _F	2.2	3		I _F = 40 A, T _J = 175 °C		
Reverse Current		45	300		V _R = 1200 V, T _J = 25 °C	Fig. 2	
	I _R	75	500	μΑ	V _R = 1200 V, T _J = 175 °C		
Total Capacitive Charge	Q _c	167		nC	V _R = 800 V, T _J = 25 °C	Fig. 5	
		2,809			$V_R = 0 \text{ V}, T_J = 25 \text{ °C}, f = 1 \text{ MHz}$		
Total Capacitance	С	174		pF	$V_R = 400 \text{ V}, T_J = 25 \text{ °C}, f = 1 \text{ MHz}$	- I	
		145			$V_R = 800 \text{ V}, T_J = 25 \text{ °C}, f = 1 \text{ MHz}$		
Capacitance Stored Energy	E _c	36		μJ	V _R = 800 V	Fig. 7	

Note

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

Thermal & Mechanical Characteristics

Parameter	Symbol	Value	Units	Note
Thermal Resistance, Junction to Case (Typ.)	R _{e, JC}	0.225	°C / W	
Operating Junction & Storage Temperature	T_{J} , T_{stg}	-55 to +175	· C	Fig. 8
Maximum Processing Temperature	T _{PROC}	325		10 min. Maximum

Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Value	
Human Body Model	НВМ	Class 3B (≥ 8000 V)	
Charge Device Model	CDM	Class C3 (≥ 1000 V)	



Typical Performance

Figure 1. Forward Characteristics

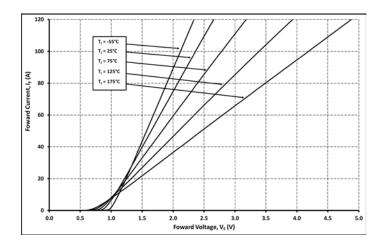


Figure 3. Current Derating

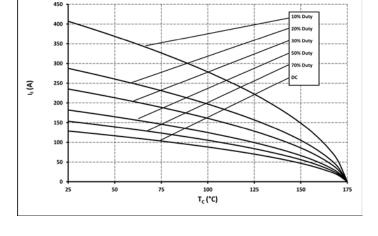


Figure 5. Total Capacitance Charge vs. Reverse Voltage

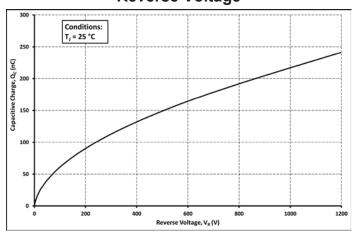


Figure 2. Reverse Characteristics

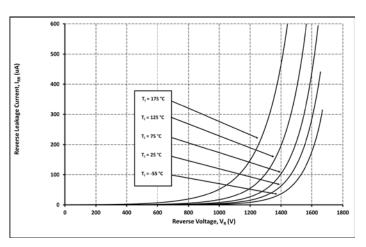


Figure 4. Power Derating

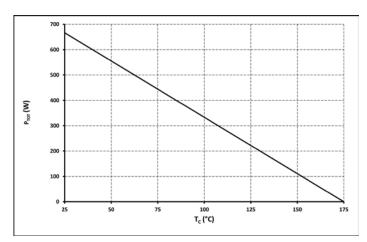
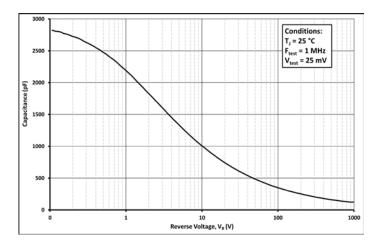


Figure 6. Capacitance vs. Reverse Voltage





Typical Performance

Figure 7. Capacitance Stored Energy

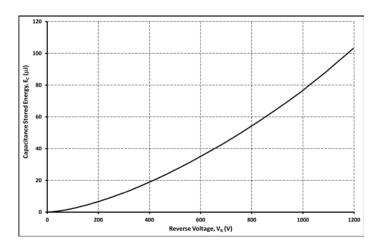
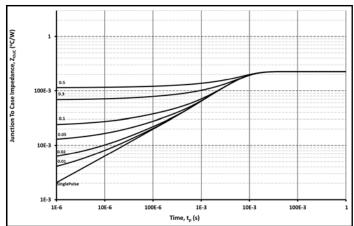


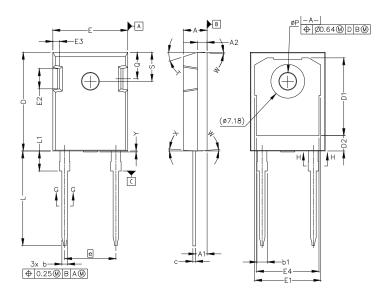
Figure 8. Transient Thermal Impedance





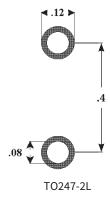
Package Dimensions

Package: TO247-2L All dimensions in mm.

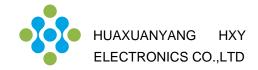


0.44	MILLIM	ETERS	INCHES		
SYM	MIN	MAX	MIN	MAX	
A	4.83	5.21	.190	.205	
A1	2.29	2.54	.090	.100	
A2	1.91	2.16	.075	.085	
b'	1.07	1.28	.042	.050	
b	1.07	1.33	.042	.052	
b1	1.91	2.41	.075	.095	
b2	1.91	2.16	.075	.085	
c'	0.55	0.65	.022	.026	
С	0.55	0.68	.022	.027	
D	20.80	21.10	.819	.831	
D1	16.25	17.35	.640	.683	
D2	2.86	3.16	.112	.124	
Е	15.75	16.13	.620	.635	
E1	13.10	14.15	.516	.557	
E2	3.68	5.10	.145	.201	
E3	1.00	1.90	.039	.075	
E4	12.38	13.43	.487	.529	
e	10.88	BSC	.428 BSC		
L	19.81	20.32	.780	.800	
L1	4.10	4.40	.161	.173	
φP	3.51	3.65	.138	.144	
Q	5.49	6.00	.216	.236	
S	6.04	6.30	.238	.248	
T	17.5° REF.				
W	3.5° REF.				
X	4° REF.				
Y	0	0.50	0	0.020	

Recommended Solder Pad Layout



all units are in inches



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